

[DOUBLE-TRIGGERED SILICON CONTROLLING RECTIFIER AND ELECTRO-STATIC DISCHARGE PROTECTION CIRCUIT THEREOF]

Abstract

A double-triggered silicon controller rectifier (SCR) comprises a plurality of N⁺ diffusion areas, a plurality of P⁺ diffusion areas, a first N-well region, a second N-well region and a third N-well region formed in a P-substrate. The N⁺ diffusion areas and the P⁺ diffusion areas are isolated by shallow trench isolation (STI) structures. Two of the N⁺ diffusion areas are N-type trigger terminals. Two of the P⁺ diffusion areas are the P-type trigger terminal.